

N0016S Process Geometry

Features

- Low Input Capacitance: 3.5pF Typical
- Low Gate Leakage: 10pA Typical
- High Breakdown Voltage: -60V Typical
- High Input Impedance
- Small Die: 391um X 391um X 203um
- Bond Pads: 90um X 90um
- Substrate Connected to Gate
- Au Back Side Finish

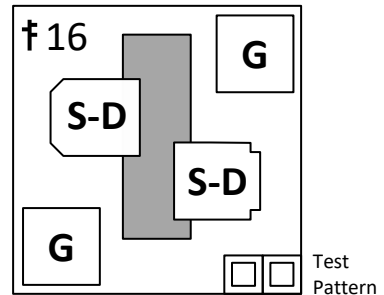
Applications

- Small Signal Amplifiers
- Audio Amplifiers
- Custom Part Options

Description

The InterFET N0016S Geometry is targeted for general purpose amplifiers and audio applications. The low input capacitance makes it ideal for mid-frequency applications.

Geometry Top View



Standard Parts

Product Summary

| Parameters | Min | Typ | Max | Unit |
|---|------|------|-----|------|
| BV _{GSS} Gate to Source Breakdown Voltage | -50 | -60 | | V |
| I _{DSS} Drain to Source Saturation Current | 0.2 | | 15 | mA |
| V _{GS(off)} Gate to Source Cutoff Voltage | -0.8 | | -6 | V |
| G _{FS} Forward Transconductance | | 3300 | | μS |

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

| Parameters | Min | Typ | Max | Unit |
|--|-----|-----|-----|------|
| V _{RGS} Reverse Gate to Source or Drain Voltage | -50 | -60 | | V |
| I _{FG} Continuous Forward Gate Current | | | 10 | mA |
| T _J Operating Junction Temperature | -55 | | 150 | °C |
| T _{STG} Storage Temperature | -65 | | 175 | °C |



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

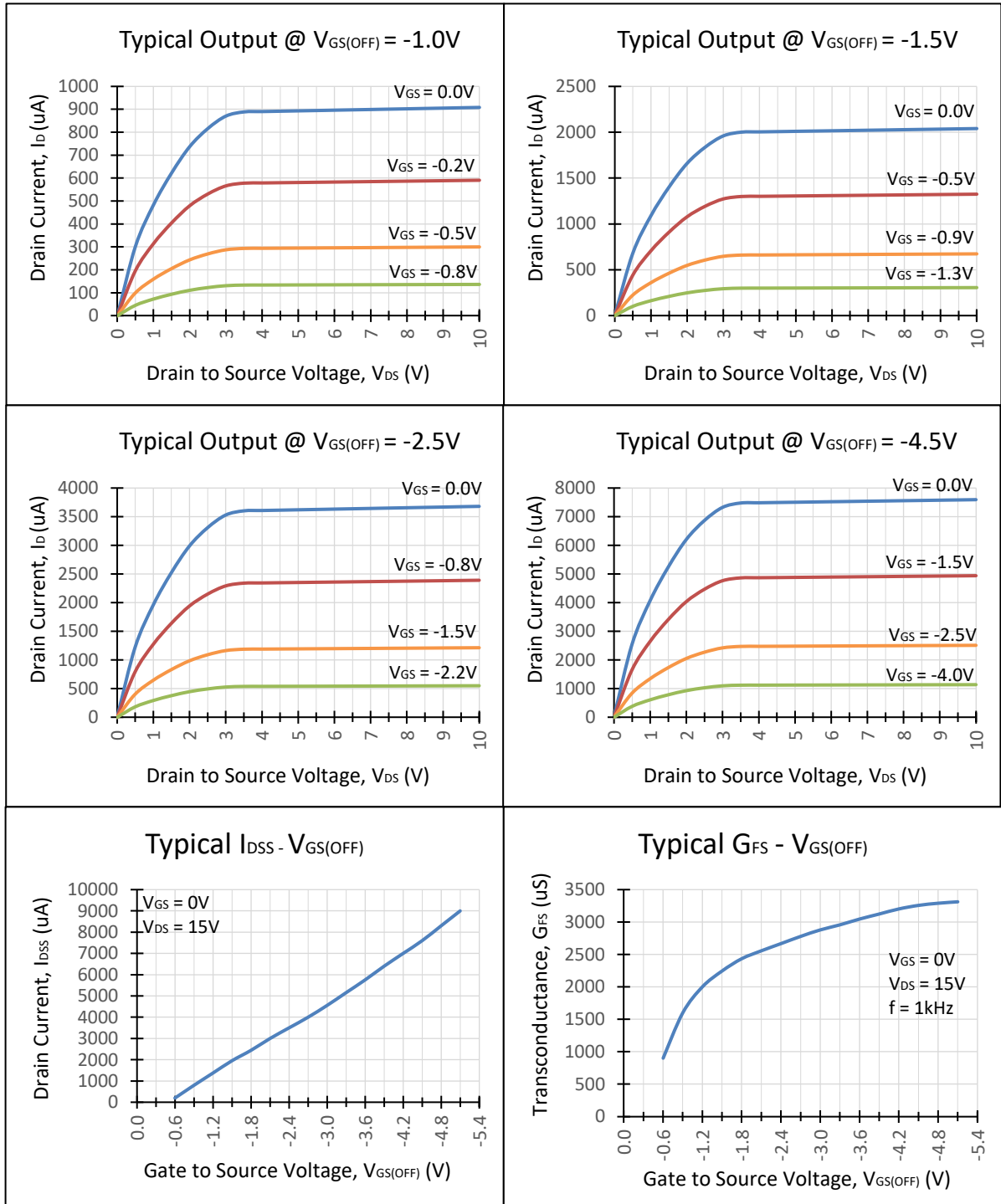
Static Characteristics (@ TA = 25°C, Unless otherwise specified)

| Parameters | Conditions | Min | Typ | Max | Unit |
|--|--|------|-----|------|------|
| BV _{GSS} Gate to Source Breakdown Voltage | I _G = -1μA, V _{DS} = 0V | -50 | -60 | | V |
| I _{GSS} Gate to Source Reverse Current | V _{GS} = -30V, V _{DS} = 0V | | -10 | -100 | pA |
| V _{GS(OFF)} Gate to Source Cutoff Voltage | V _{DS} = 15V, I _D = 1nA | -0.8 | | -6.0 | V |
| I _{DSS} Drain to Source Saturation Current | V _{DS} = 15V, V _{GS} = 0V | 0.2 | | 15 | mA |

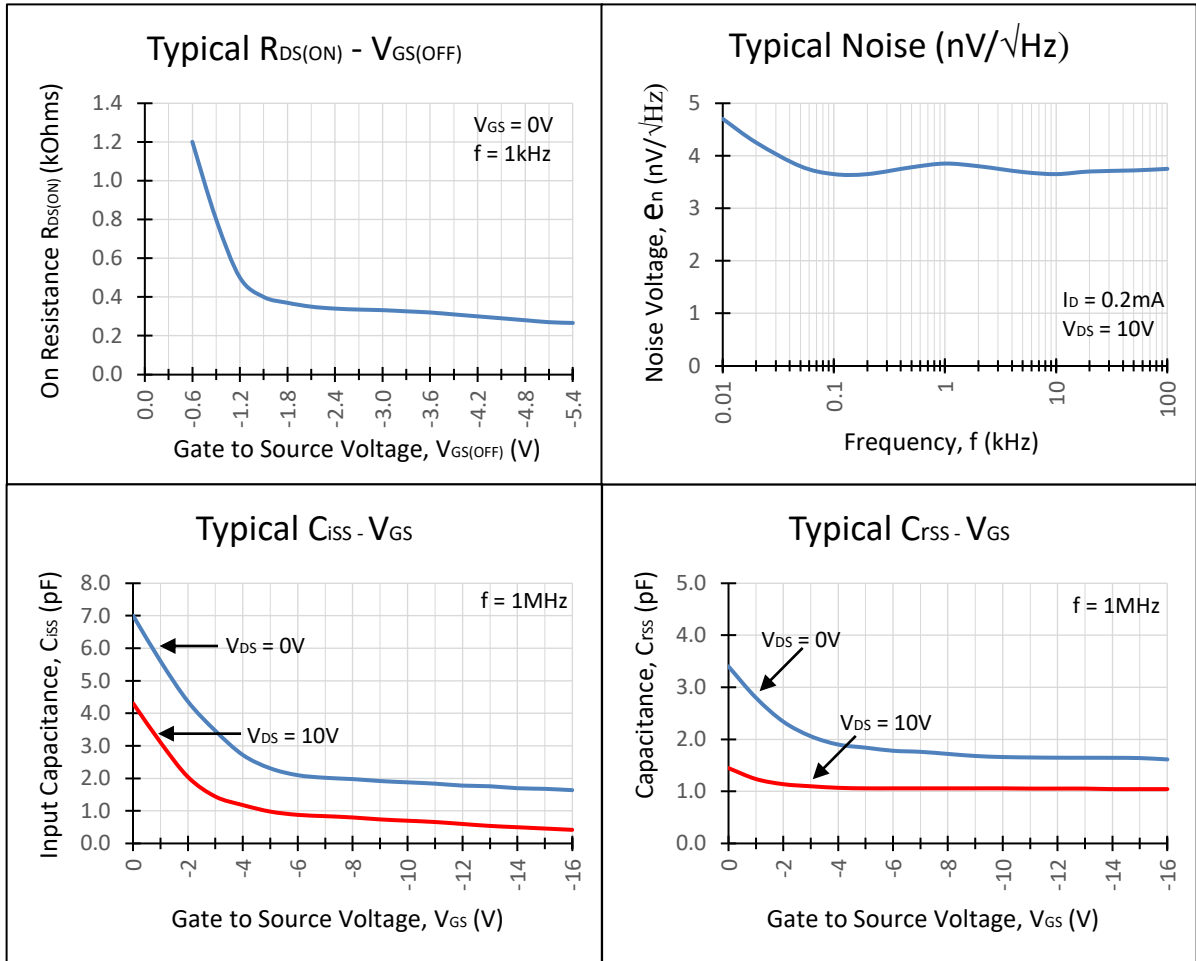
Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

| Parameters | Conditions | Min | Typ | Max | Unit |
|--|---|-----|------|-----|--------|
| G _{FS} Forward Transconductance | V _{DS} = 15V, V _{GS} = 0 V, f = 1kHz | | 3300 | | μS |
| C _{iss} Input Capacitance | V _{DS} = 15V, V _{GS} = 0 V, f = 1MHz | | 3.5 | | pF |
| C _{rss} Reverse Transfer Capacitance | V _{DS} = 15V, V _{GS} = 0 V, f = 1MHz | | 1.2 | | pF |
| e _n Noise Voltage | V _{DS} = 10V, I _D = 0.2mA f = 1kHz | | 4.2 | | nV/√Hz |

Typical N0016S Characteristics

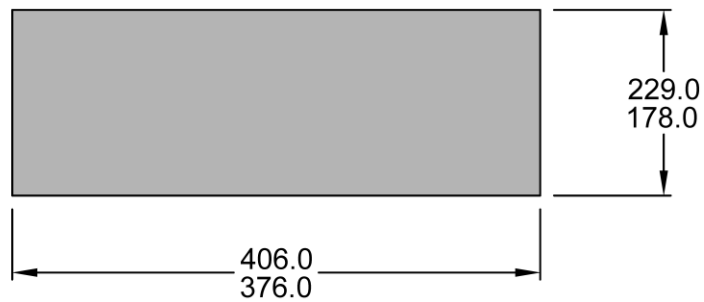
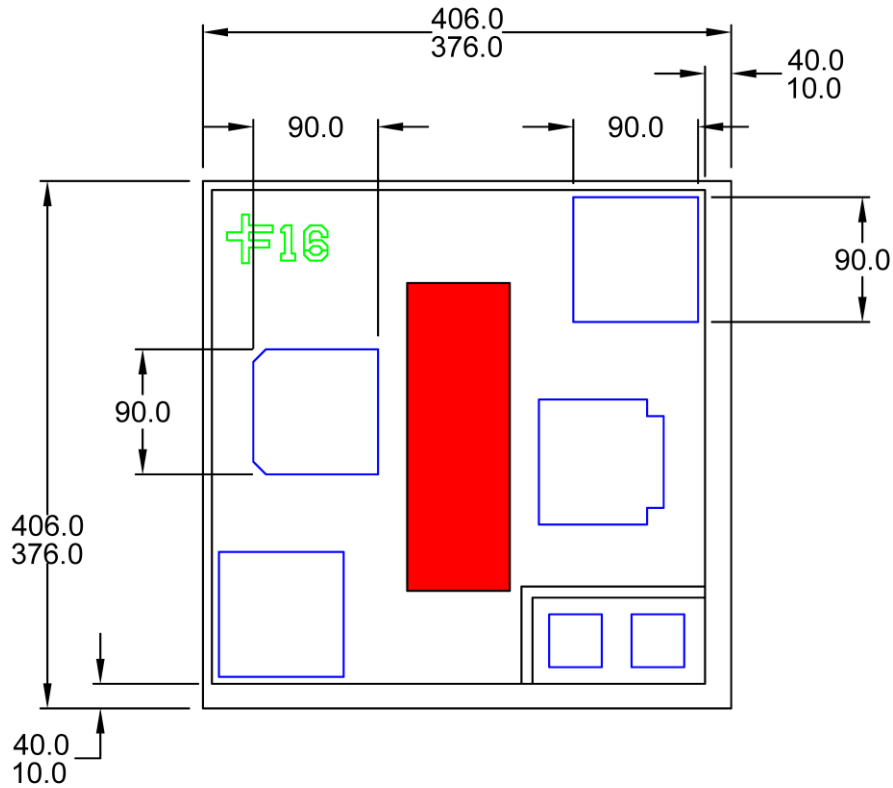


Typical N0016S Characteristics (Continued)



N0016S Die Geometry Mechanical

Raw Die Dimensions



1. All linear dimensions are in micrometers.